

Silicon NPN Power Transistors

BU608

DESCRIPTION

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- With TO-3 package
- High voltage
- Wide area of safe operation

APPLICATIONS

- For TV horizontal deflection output applications

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

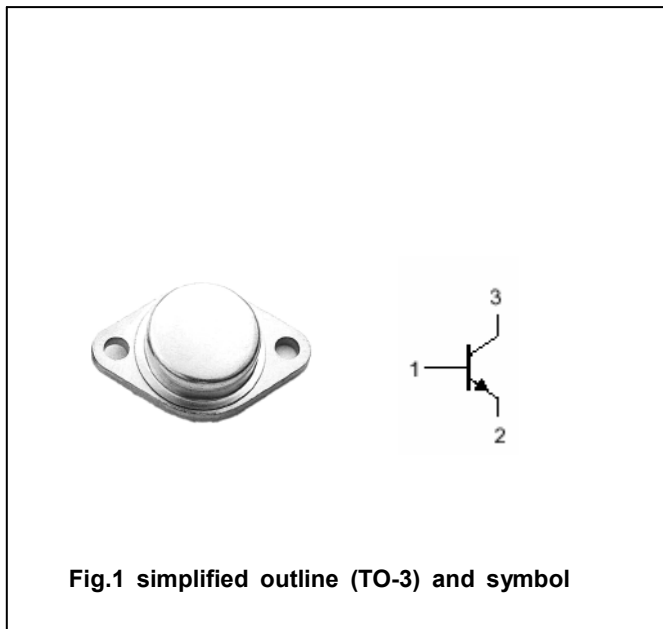


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	400	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		7	A
P _C	Collector power dissipation	T _a =25°C	2.5	W
		T _C =25°C	100	
T _j	Junction temperature		200	°C
T _{stg}	Storage temperature		-65~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.75	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =100mA ; I _B =0	200			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA; I _E =0	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A ; I _B =1.2A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A ; I _B =1.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =400V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =7A ; V _{CE} =5V	5			

PACKAGE OUTLINE

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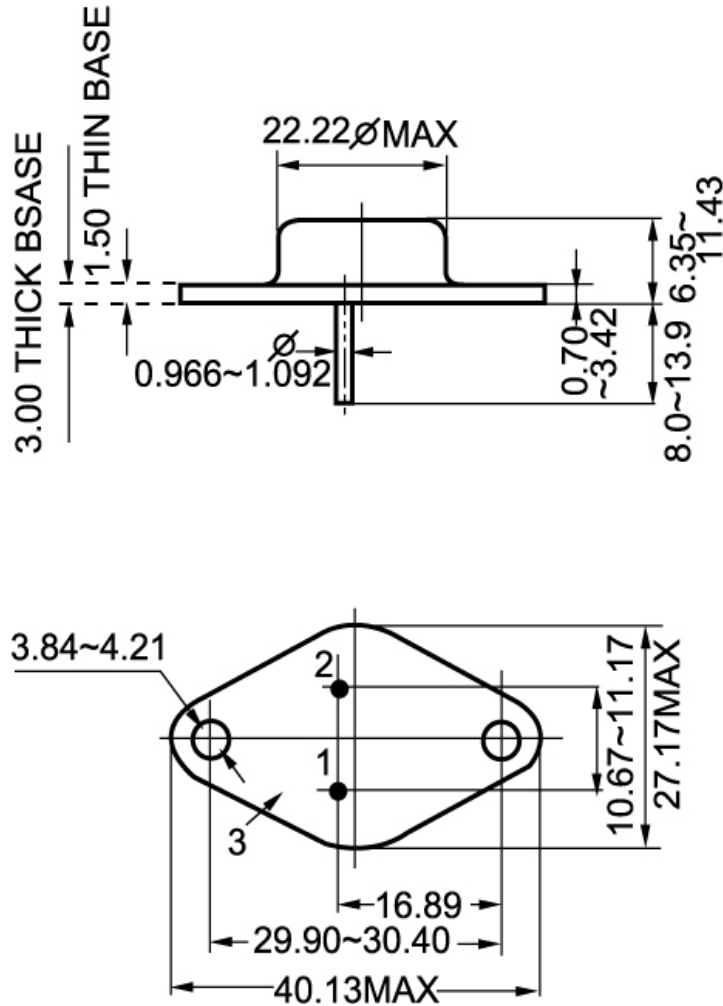


Fig.2 Outline dimensions